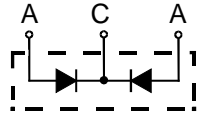
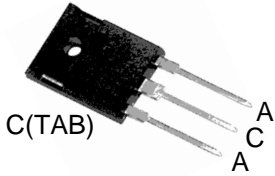


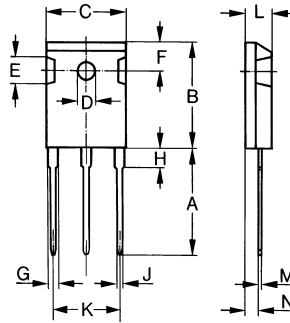
SBL2050PT thru SBL2060PT

Low V_F Schottky Barrier Rectifiers



A=Anode, C=Cathode, TAB=Cathode

Dimensions TO-247AD



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

	V_{RRM}	V_{RMS}	V_{DC}
	V	V	V
SBL2050PT	50	35	50
SBL2060PT	60	42	60

Symbol	Characteristics	Maximum Ratings	Unit
I_{AV}	Maximum Average Forward Rectified Current @ $T_c=95^\circ\text{C}$	20	A
I_{FSM}	Peak Forward Surge Current 8.3ms Single Half-Sine-Wave Superimposed On Rated Load (JEDEC METHOD)	250	A
V_F	Maximum Forward Voltage At 10A DC (Note 1)	0.75	V
I_R	Maximum DC Reverse Current @ $T_J=25^\circ\text{C}$ At Rated DC Blocking Voltage @ $T_J=100^\circ\text{C}$	1 50	mA
C_J	Typical Junction Capacitance Per Element (Note 2)	600	pF
$R_{\theta JC}$	Typical Thermal Resistance (Note 3)	2.5	$^\circ\text{C}/\text{W}$
T_J	Operating Temperature Range	-55 to +125	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$

NOTES: 1. 300us Pulse Width, 2% Duty Cycle.
2. Measured At 1.0MHz And Applied Reverse Voltage Of 4.0V DC.
3. Thermal Resistance Junction To Case.

FEATURES

- * Metal of silicon rectifier, majority carrier conduction
- * Guard ring for transient protection
- * Low power loss, high efficiency
- * High current capability, low V_F
- * High surge capacity
- * For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- * Case: TO-247AD molded plastic
- * Polarity: As marked on the body
- * Weight: 0.2 ounces, 5.6 grams
- * Mounting position: Any

SBL2050PT thru SBL2060PT

Low V_F Schottky Barrier Rectifiers

